

# BCR10PM-12LA

Triac

Medium Power Use

R07DS0104EJ0300 (Previous: REJ03G0304-0200)

Rev.3.00 Sep 13, 2010

#### **Features**

I<sub>T (RMS)</sub>: 10 A
 V<sub>DRM</sub>: 600 V

•  $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGT III}$ : 30 mA (20 mA)<sup>Note5</sup>

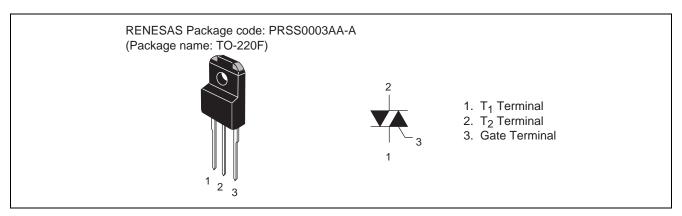
• Viso: 2000 V

• Insulated Type

• Planar Passivation Type

UL Recognised: Yellow Card No. E223904

#### **Outline**



## **Applications**

Switching mode power supply, light dimmer, electronic flasher unit, hair drier, control of household equipment such as TV sets, stereo systems, refrigerator, washing machine, infrared kotatsu, carpet, small motor control, solid state relay, copying machine, electric tool, electric heater, solenoid driver, and other general controlling devices

#### **Maximum Ratings**

| Parameter                                              | Symbol    | Voltage class | Unit |  |
|--------------------------------------------------------|-----------|---------------|------|--|
| Faranietei                                             | Зуппоп    | 12            |      |  |
| Repetitive peak off-state voltage <sup>Note1</sup>     | $V_{DRM}$ | 600           | V    |  |
| Non-repetitive peak off-state voltage <sup>Note1</sup> | $V_{DSM}$ | 720           | V    |  |

| Parameter                      | Symbol               | Ratings      | Unit             | Conditions                                                               |
|--------------------------------|----------------------|--------------|------------------|--------------------------------------------------------------------------|
| RMS on-state current           | I <sub>T (RMS)</sub> | 10           | А                | Commercial frequency, sine full wave 360° conduction, Tc = 85°C          |
| Surge on-state current         | I <sub>TSM</sub>     | 100          | А                | 60Hz sinewave 1 full cycle, peak value, non-repetitive                   |
| I <sup>2</sup> t for fusing    | l <sup>2</sup> t     | 41.6         | A <sup>2</sup> s | Value corresponding to 1 cycle of half wave 60Hz, surge on-state current |
| Peak gate power dissipation    | $P_{GM}$             | 5            | W                |                                                                          |
| Average gate power dissipation | P <sub>G (AV)</sub>  | 0.5          | W                |                                                                          |
| Peak gate voltage              | $V_{GM}$             | 10           | V                |                                                                          |
| Peak gate current              | I <sub>GM</sub>      | 2            | А                |                                                                          |
| Junction temperature           | Tj                   | - 40 to +125 | °C               |                                                                          |
| Storage temperature            | Tstg                 | - 40 to +125 | °C               |                                                                          |
| Mass                           | _                    | 2.0          | g                | Typical value                                                            |
| Isolation voltage              | Viso                 | 2000         | V                | Ta = 25°C, AC 1 minute,<br>$T_1 \cdot T_2 \cdot G$ terminal to case      |

Notes: 1. Gate open.

#### **Electrical Characteristics**

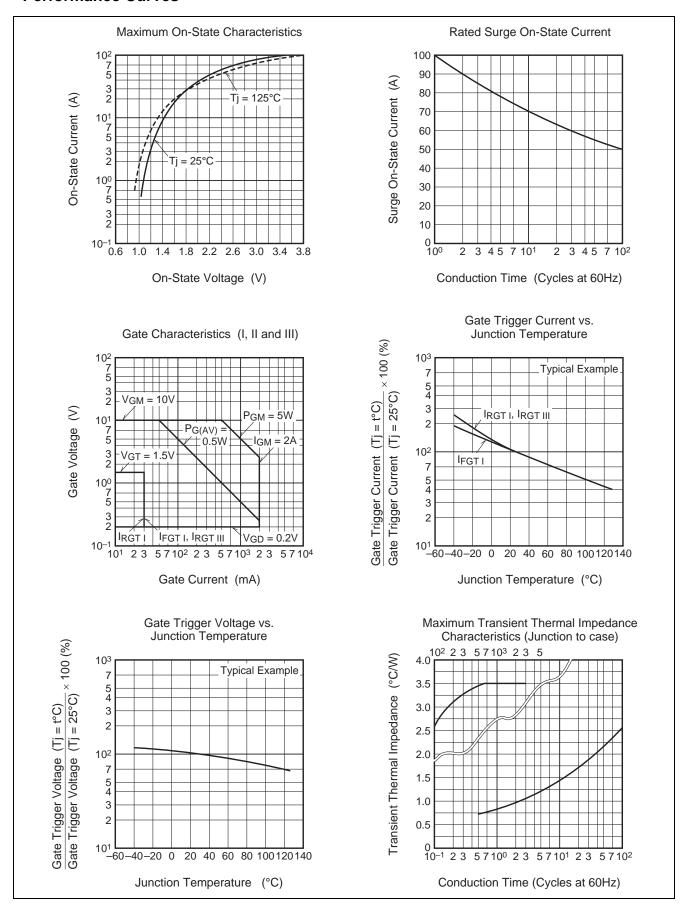
| Parameter                                                    |      | Symbol                      | Min. | Тур. | Max.                | Unit | Test conditions                         |
|--------------------------------------------------------------|------|-----------------------------|------|------|---------------------|------|-----------------------------------------|
| Repetitive peak off-state cur                                | rent | I <sub>DRM</sub>            | _    | _    | 2.0                 | mA   | Tj = 125°C, V <sub>DRM</sub> applied    |
| On-state voltage                                             |      | $V_{TM}$                    | _    | _    | 1.5                 | V    | $Tc = 25^{\circ}C$ , $I_{TM} = 15 A$ ,  |
|                                                              |      |                             |      |      |                     |      | Instantaneous measurement               |
| Gate trigger voltage <sup>Note2</sup>                        | I    | $V_{FGTI}$                  |      | _    | 1.5                 | V    | $Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω, |
|                                                              | II   | $V_{RGT_{I}}$               |      | _    | 1.5                 | V    | $R_G = 330 \Omega$                      |
|                                                              | III  | $V_{RGTIII}$                | _    | _    | 1.5                 | V    |                                         |
| Gate trigger current <sup>Note2</sup>                        | I    | $I_{\text{FGT}_{\text{I}}}$ | _    | _    | 30 <sup>Note5</sup> | mA   | $Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω, |
|                                                              | II   | $I_{RGT_{\mathrm{I}}}$      |      | _    | 30 <sup>Note5</sup> | mA   | $R_G = 330 \Omega$                      |
|                                                              | III  | $I_{RGTIII}$                | _    | _    | 30 <sup>Note5</sup> | mA   |                                         |
| Gate non-trigger voltage                                     |      | $V_{GD}$                    | 0.2  | _    | _                   | V    | $Tj = 125$ °C, $V_D = 1/2 V_{DRM}$      |
| Thermal resistance                                           |      | R <sub>th (j-c)</sub>       | _    | _    | 3.5                 | °C/W | Junction to case <sup>Note3</sup>       |
| Critical-rate of rise of off-state commutating voltage Note4 | е    | (dv/dt)c                    | 10   | _    |                     | V/μs | Tj = 125°C                              |

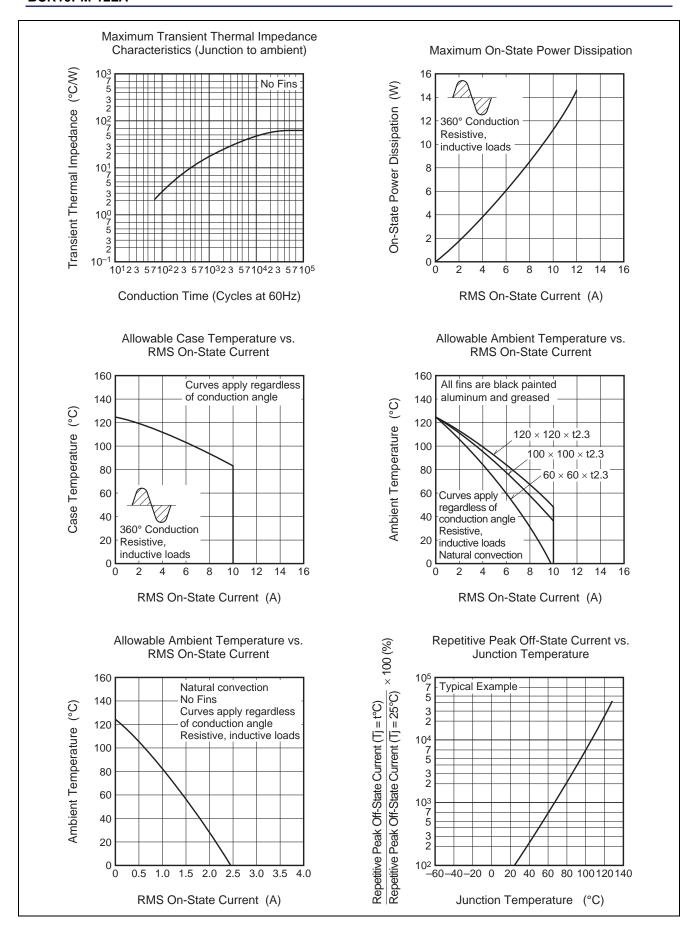
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

- 3. The contact thermal resistance  $R_{th\ (c\text{-}f)}$  in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
- 5. High sensitivity ( $I_{GT} \le 20$  mA) is also available. ( $I_{GT}$  item: 1)

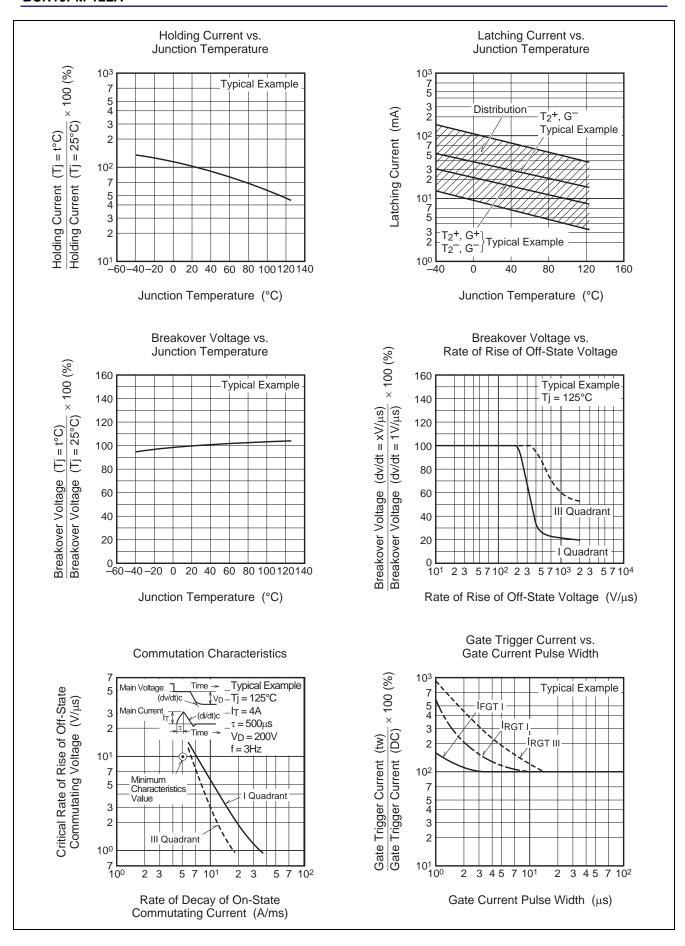
| Test conditions                                                        | Commutating voltage and current waveforms (inductive load) |
|------------------------------------------------------------------------|------------------------------------------------------------|
| 1. Junction temperature Tj = 125°C                                     | Supply Voltage  →Time                                      |
| 2. Rate of decay of on-state commutating current (di/dt)c = - 5.0 A/ms | Main Current (di/dt)c  Time                                |
| 3. Peak off-state voltage $V_D = 400 \text{ V}$                        | Main Voltage — Time (dv/dt)c                               |

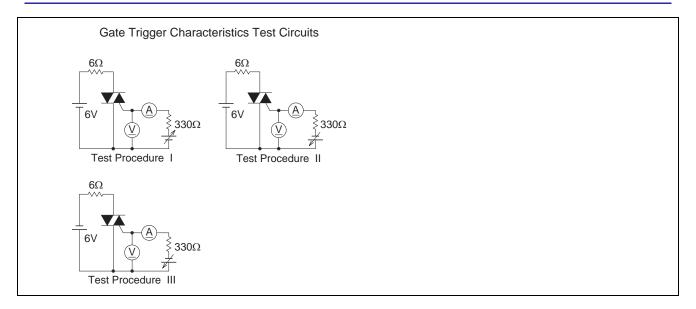
#### **Performance Curves**



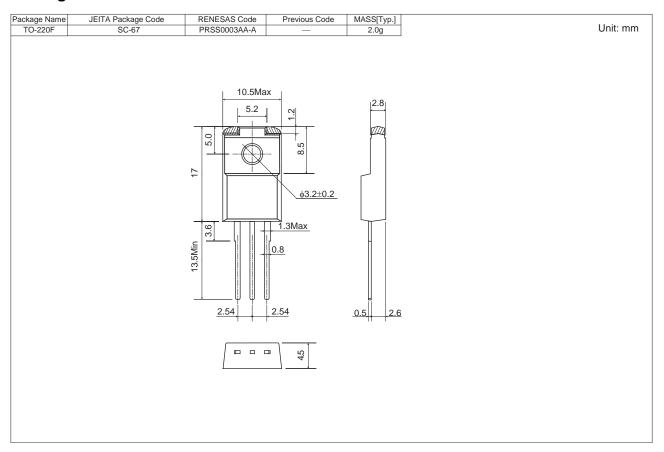


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## **Package Dimensions**



## **Order Code**

| Lead form     | Standard packing        | Quantity | Standard order code           | Standard order code example |
|---------------|-------------------------|----------|-------------------------------|-----------------------------|
| Straight type | Vinyl sack              | 100      | Type name                     | BCR10PM-12LA                |
| Lead form     | Plastic Magazine (Tube) | 50       | Type name – Lead forming code | BCR10PM-12LA-A8             |

Note: Please confirm the specification about the shipping in detail.

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